

HSU119

Silicon Epitaxial Planar Diode for High Speed Switching

REJ03G0190-0100Z
(Previous: ADE-208-444)
Rev.1.00
Mar.22.2004

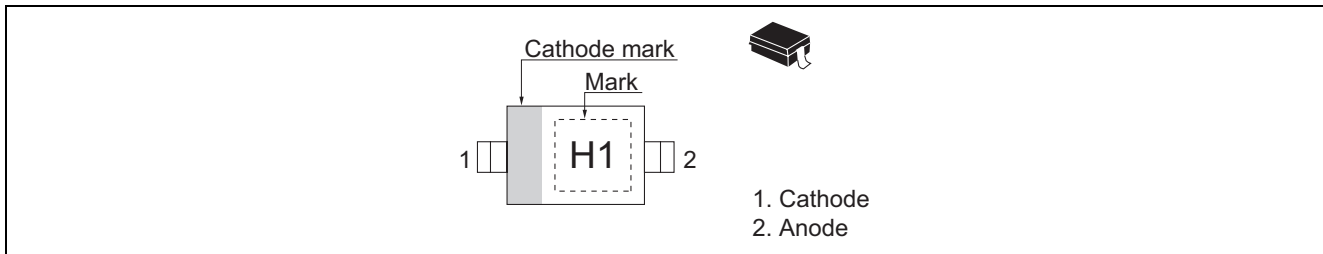
Features

- Low capacitance. ($C = 2.0$ pF max)
- Short reverse recovery time. ($t_{rr} = 3.0$ ns max)
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HSU119 | H1 | URP |

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Value | Unit |
|---|----------------|-------------|------|
| Peak reverse voltage | V_{RM} | 85 | V |
| Reverse voltage | V_R | 80 | V |
| Peak forward current | I_{FM} | 300 | mA |
| Non-Repetitive peak forward surge current | I_{FSM}^{*1} | 4 | A |
| Average rectified current | I_O | 100 | mA |
| Junction temperature | T_j | 125 | °C |
| Storage temperature | T_{stg} | -55 to +125 | °C |

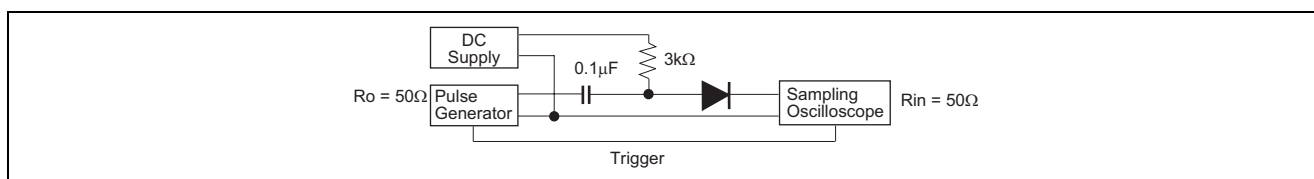
Note: 1. Within 1μs forward surge current.

Electrical Characteristics

(Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------------------------|----------|-----|-----|-----|------|---|
| Forward voltage | V_{F1} | — | — | 0.8 | V | $I_F = 10 \text{ mA}$ |
| | V_{F2} | — | — | 1.2 | V | $I_F = 100 \text{ mA}$ |
| Reverse current | I_R | — | — | 0.1 | μA | $V_R = 80 \text{ V}$ |
| Capacitance | C | — | — | 2.0 | pF | $V_R = 0 \text{ V}, f = 1 \text{ MHz}$ |
| Reverse recovery time* ¹ | t_{rr} | — | — | 3.0 | ns | $I_F = 10 \text{ mA}, V_R = 6 \text{ V}, R_L = 50 \Omega$ |

Note: 1. Reverse recovery time test circuit



Main Characteristics

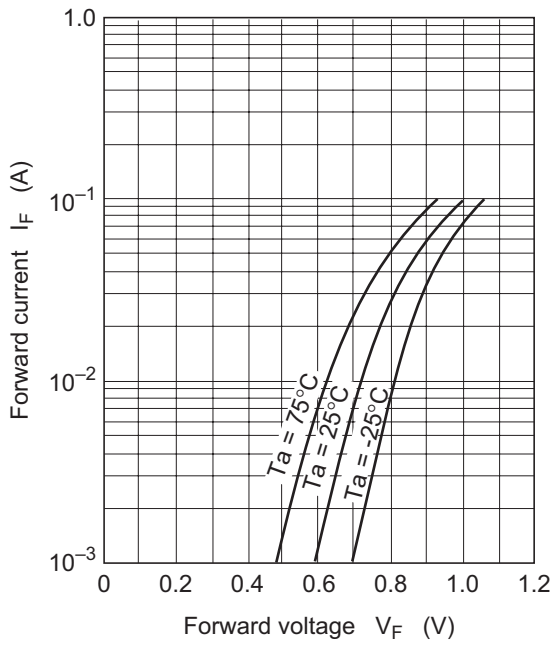


Fig.1 Forward current vs. Forward voltage

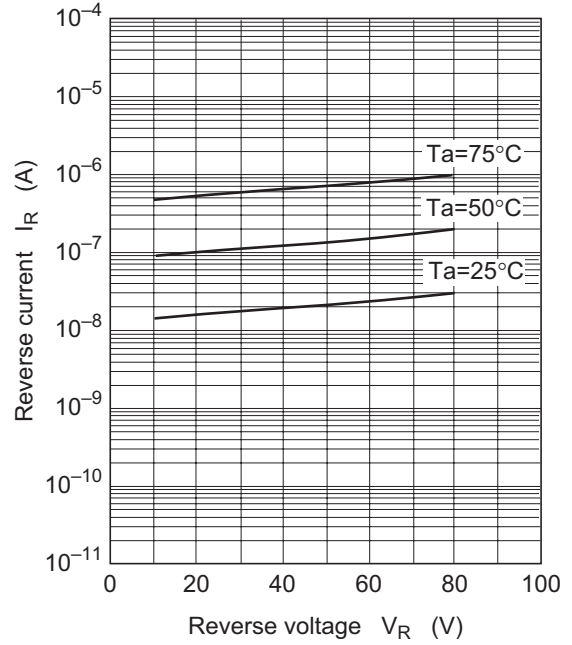


Fig.2 Reverse current vs. Reverse voltage

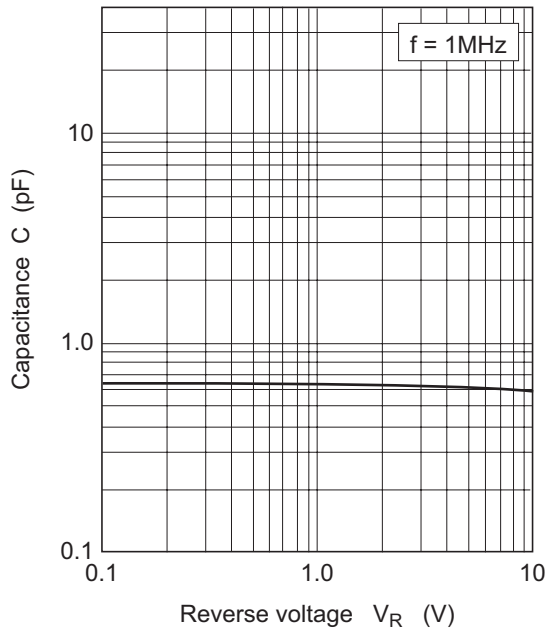
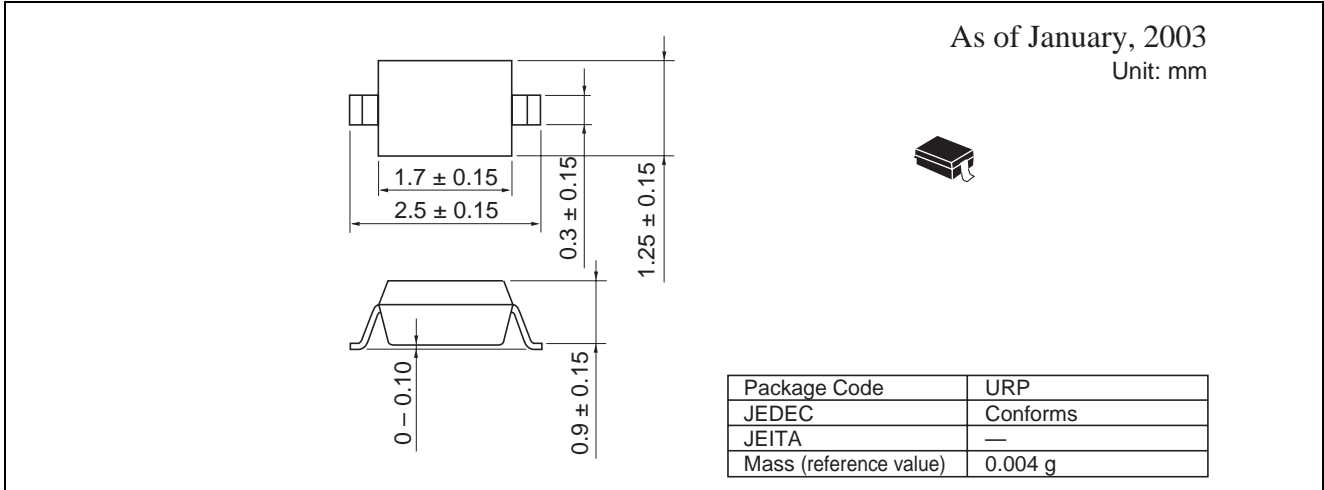


Fig.3 Capacitance vs. Reverse voltage

Package Dimensions



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